SamHop Microelectronics Corp.

STG8211

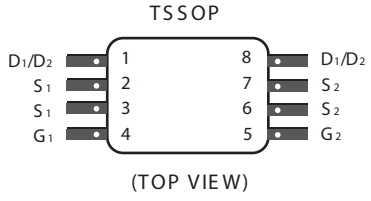
Jan,09,2019 Ver 1.3

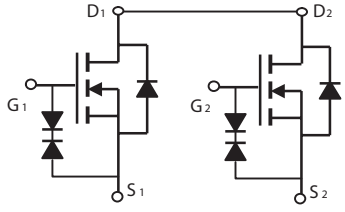
Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
20V	10A	13.5 @ V_{GS} = 4.0V 18 @ V_{GS} = 2.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous [a] @ T_J=25°C	I_D	10	A
-Pulsed [b]	I_{DM}	40	A
Drain-Source Diode Forward Current [a]	I_S	1.7	A
Maximum Power Dissipation [a]	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient [a]	$R_{\theta JA}$	85	°C/W

STG8211

ELECTRICAL CHARACTERISTICS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V, V_{GS}=0V			1	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=±12V,V_{DS}=0V			±10	uA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	0.5	0.8	1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4V, I_D=5A	8.5	11	13.5	m ohm
		V_{GS}=2.5V, I_D=3A	10	13.5	18	m ohm
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=5A		22		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS}=8V, V_{GS}=0V f=1.0MHz		1815		pF
Output Capacitance	C_{OSS}			406		pF
Reverse Transfer Capacitance	C_{RSS}			255		pF
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD}=10V, I_D=1A, V_{GEN}=4V, R_L=10 ohm R_{GEN}=10 ohm		31		ns
Rise Time	t_r			62		ns
Turn-Off Delay Time	$t_{D(OFF)}$			96		ns
Fall Time	t_f			40		ns
Total Gate Charge	Q_g	V_{DS}=10V, I_D=5A, V_{GS}=4V		19		nC
Gate-Source Charge	Q_{gs}			3.5		nC
Gate-Drain Charge	Q_{gd}			6.7		nC

STG8211

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS [b]						
Diode Forward Voltage	V_{SD}	V_{GS} = 0V, Is =1.7A		0.75	1.2	V

Notes

a.Surface Mounted on FR4 Board, t ≤ 10sec.
b.Pulse Test:Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
c.Guaranteed by design, not subject to production testing.

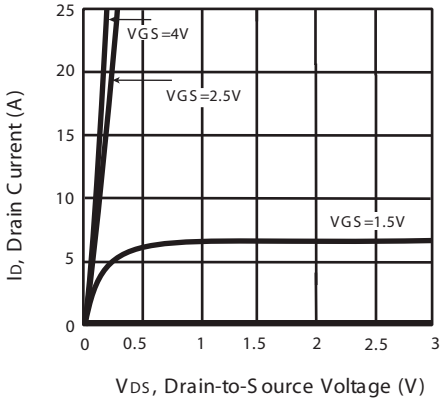


Figure 1. Output Characteristics

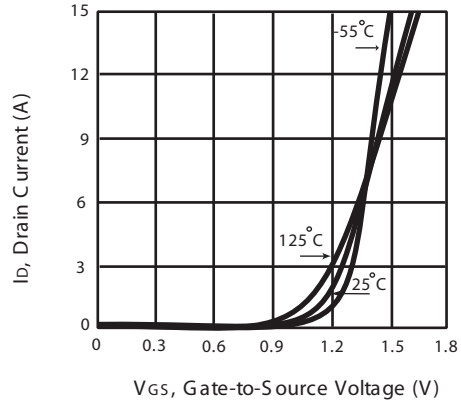


Figure 2. Transfer Characteristics

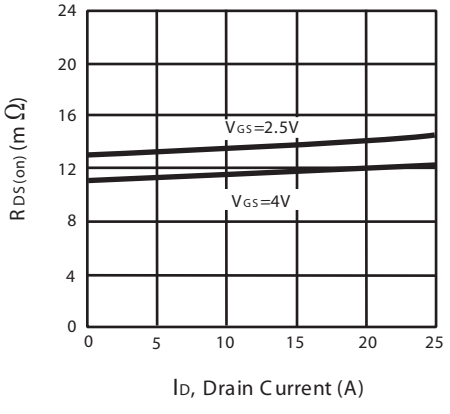


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

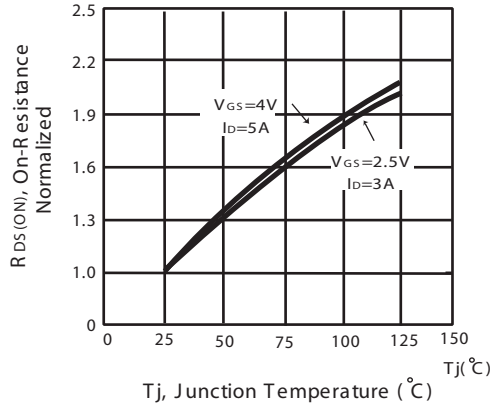


Figure 4. On-Resistance Variation with Drain Current and Temperature

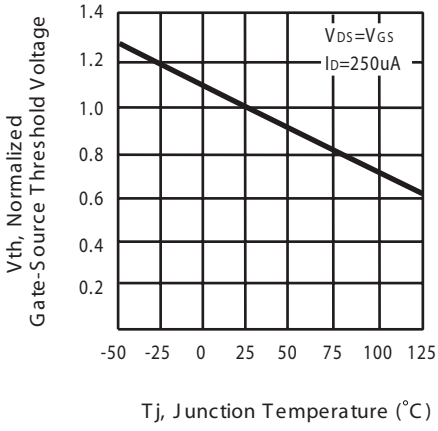


Figure 5. Gate Threshold Variation with Temperature

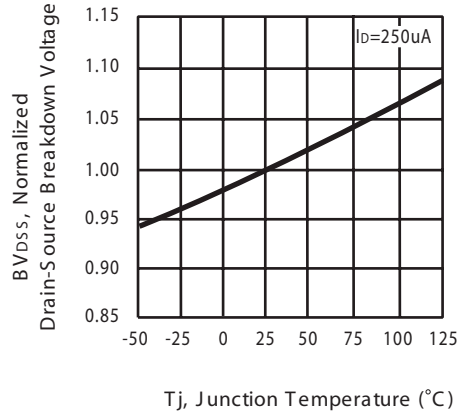


Figure 6. Breakdown Voltage Variation with Temperature

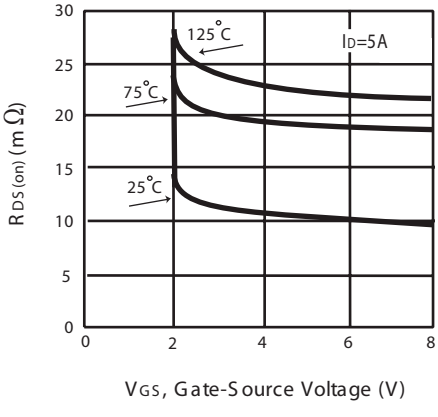


Figure 7. On-Resistance vs. Gate-Source Voltage

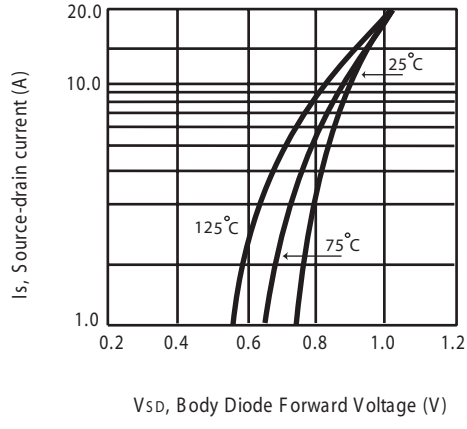


Figure 8. Body Diode Forward Voltage Variation with Source Current

STG8211

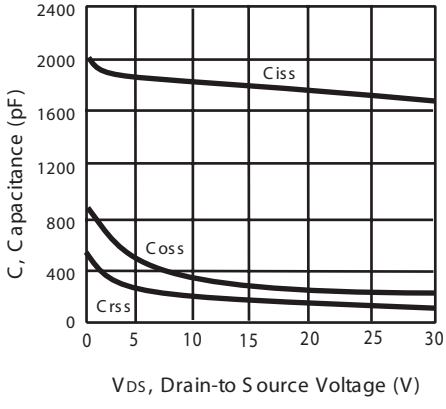


Figure 9. Capacitance

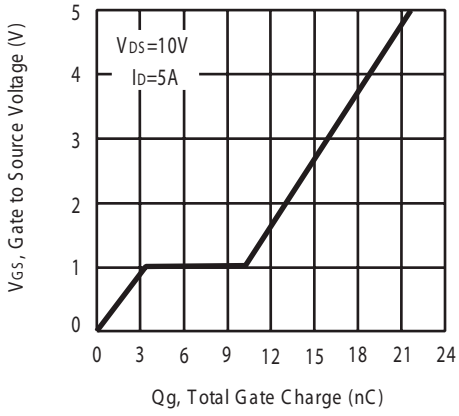


Figure 10. Gate Charge

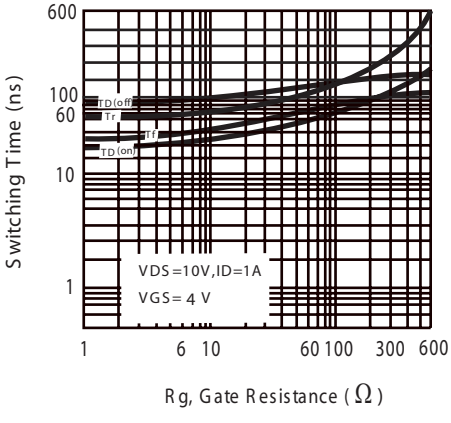


Figure 11.switching characteristics

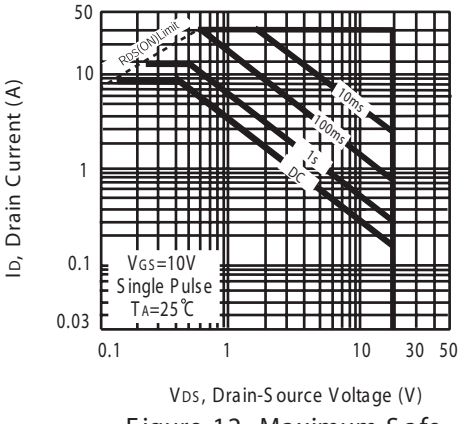


Figure 12. Maximum Safe Operating Area

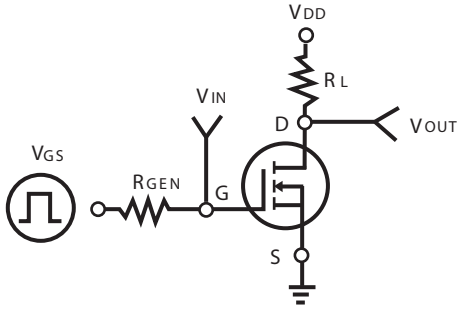


Figure 13. Switching Test Circuit

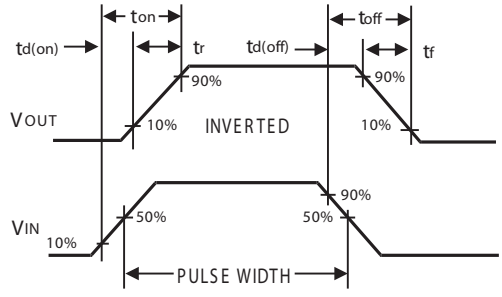


Figure 14. Switching Waveforms

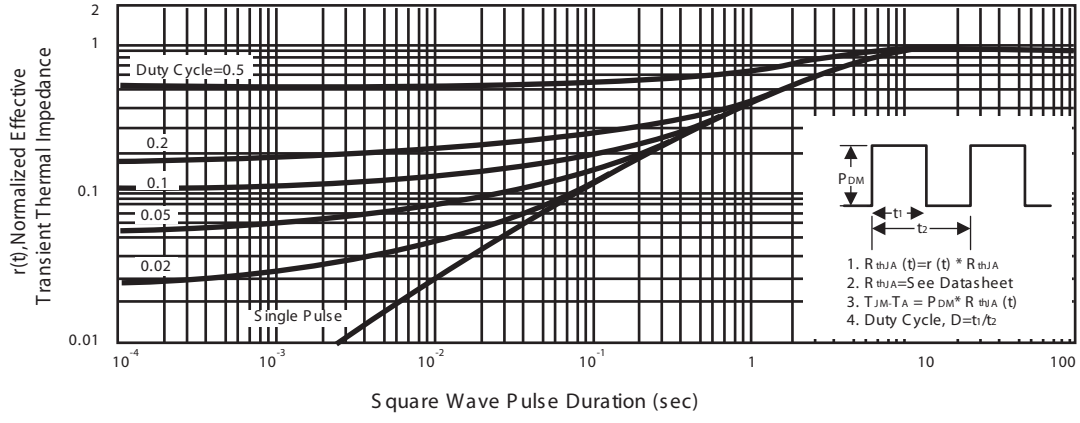
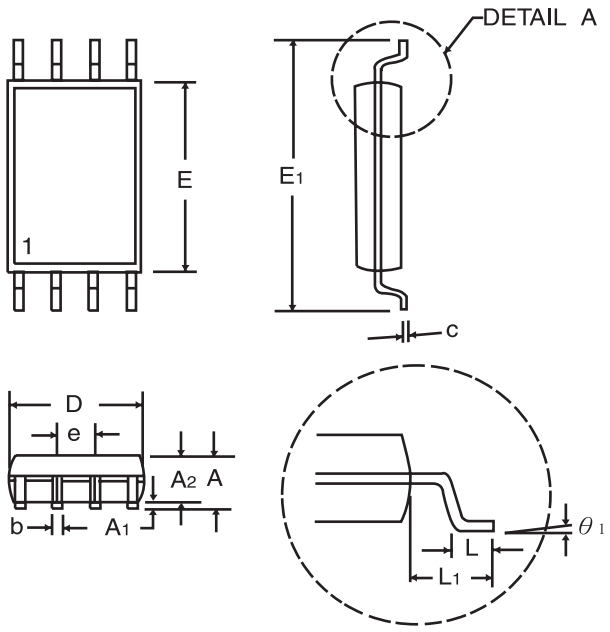


Figure 15. Normalized Thermal Transient Impedance Curve

STG8211

PACKAGE OUTLINE DIMENSIONS

TSSOP-8



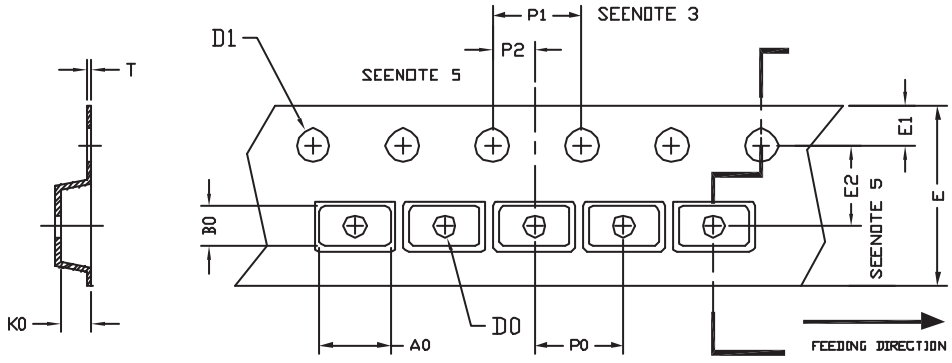
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.85	1.20	0.033	0.047
A1	0.05	0.15	0.002	0.006
A2	0.80	1.05	0.031	0.041
b	0.19	0.30	0.007	0.012
c	0.127		0.005	
D	2.90	3.10②	0.114	0.122②
E	4.30	4.50③	0.169	0.177③
E1	6.20	6.60	0.244	0.260
e	0.65BSC		0.025BSC	
L	0.50	0.70	0.020	0.028
L1	1.00		0.039	
θ_1	0°	8°	0°	8°

Notes:

1. This drawing is for general information only.
   Refer to JEDEC Drawing MO-153,Variation AA,for proper dimensions, tolerances,datums,etc.
2. Dimension D does not include mold Flash,protrusions or gate burrs.
   Mold Flash,protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
3. Dimension E does not include inter-lead Flash or protrusions.
   Inter-lead Flash and protrusions shall not exceed 0.25mm (0.010 in) per side.
4. Dimension b does not include Dambar protrusion.Allowable Dambar protrusion shall be 0.08 mm total in excess of the b dimension at maximum material condition.Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07 mm.
5. Dimension D and E to be determined at Datum Plane H.

TSSOP-8 Tape and Reel Data

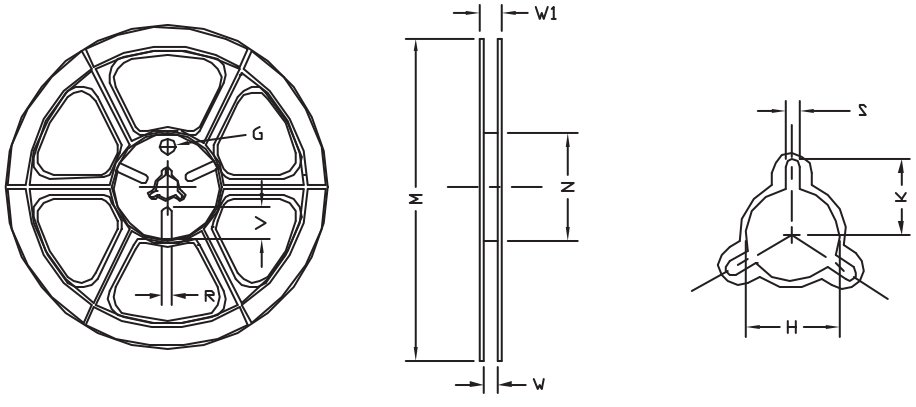
TSSOP-8 Carrier Tape



UNIT : mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TSSOP 8	6.08	4.40	1.60	ϕ 1.50 + 0.1 - 0.0	ϕ 1.50 + 0.1 - 0.0	12.00 ± 0.3	1.75	5.50 ± 0.05	8.00	4.00	2.00 ±0.05	0.30 ±0.05

TSSOP-8 Reel



UNIT : mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	ϕ 330	330	100	12.5	16.0	ϕ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---